Intel - EP20K100EQI240-2X Datasheet

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	183
Number of Gates	263000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k100eqi240-2x

Table 5. APEX 20K FineLine BGA Package Options & I/O Count *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 *(3)*	
EP20K400E				488 *(3)*	
EP20K600E				508 *(3)*	588
EP20K1000E				508 *(3)*	708
EP20K1500E					808

Notes to Tables 4 and 5:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

Table 6. APEX 20K QFP, BGA & PGA Package Sizes

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	–
Area (mm^2)	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

Table 7. APEX 20K FineLine BGA Package Sizes

Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm^2)	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

Table 8. Comparison of APEX 20K & APEX 20KE Features

Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V_{CCIO} V_{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

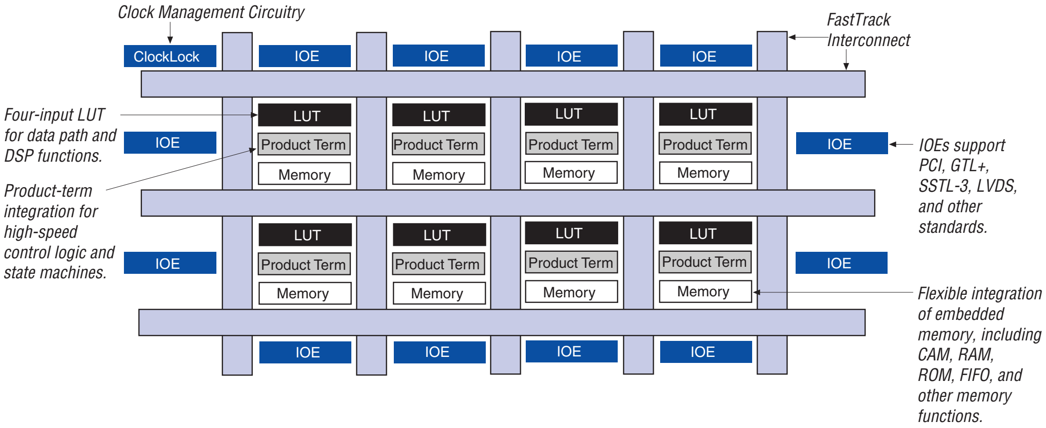
Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack® Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram

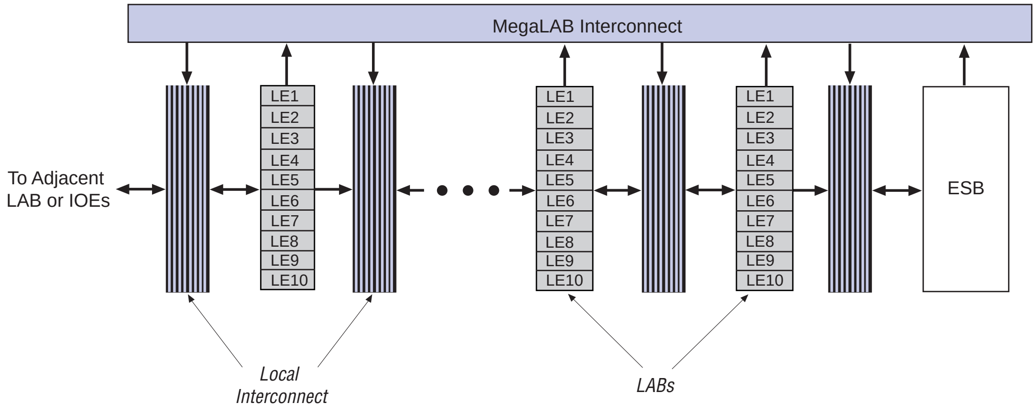


APEX 20K devices provide two dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals. These signals use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20K devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry. APEX 20KE devices provide two additional dedicated clock pins, for a total of four dedicated clock pins.

MegaLAB Structure

APEX 20K devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains a group of logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. The EP20K30E device has 10 LABs, EP20K60E through EP20K600E devices have 16 LABs, and the EP20K1000E and EP20K1500E devices have 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack Interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure



ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (`WE`) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the `WE` signal. In contrast, the ESB's synchronous RAM generates its own `WE` signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

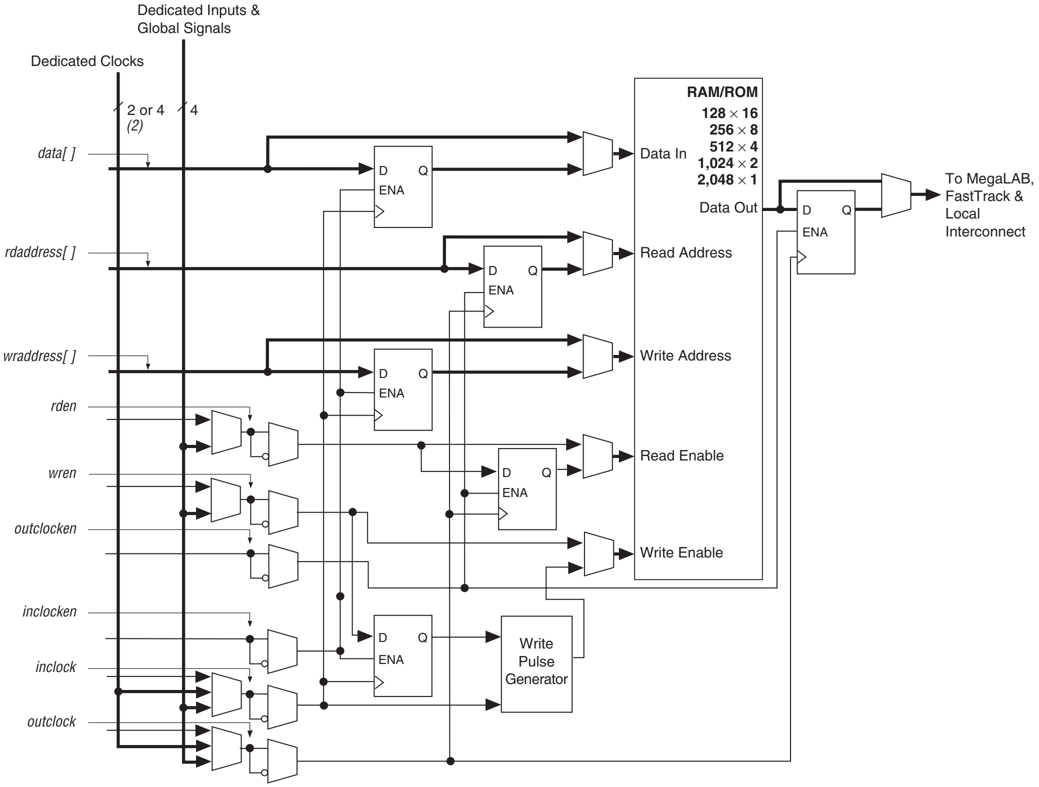
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, `WE`, and write address. The other clock controls all registers associated with reading: read enable (`RE`), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

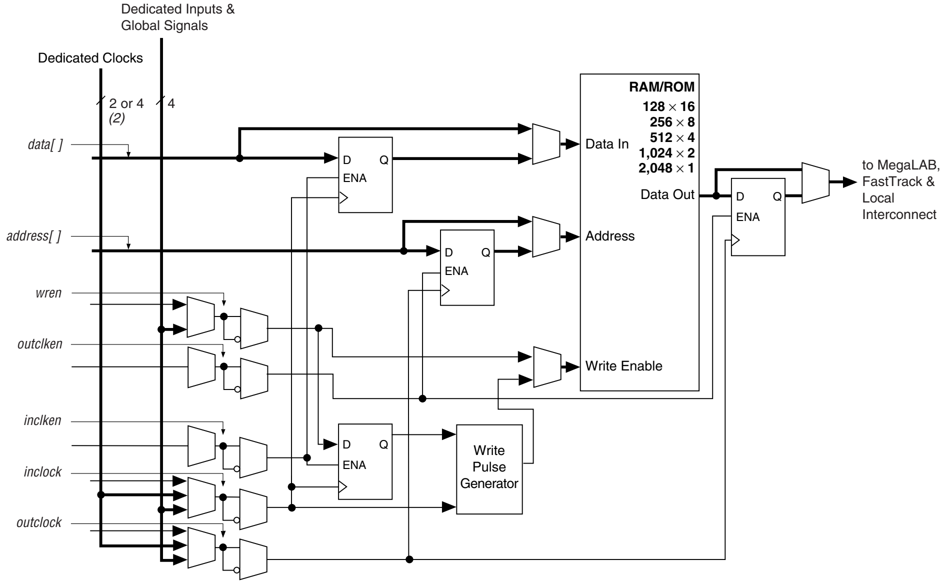
Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Notes to Figure 20:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Figure 22. ESB in Single-Port Mode   *Note (1)*



Notes to Figure 22:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.

(2) APEX 20KE devices have four dedicated clocks.

Content-Addressable Memory

In APEX 20KE devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data `FA12` is stored in address `14`, the CAM outputs `14` when `FA12` is driven into it.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

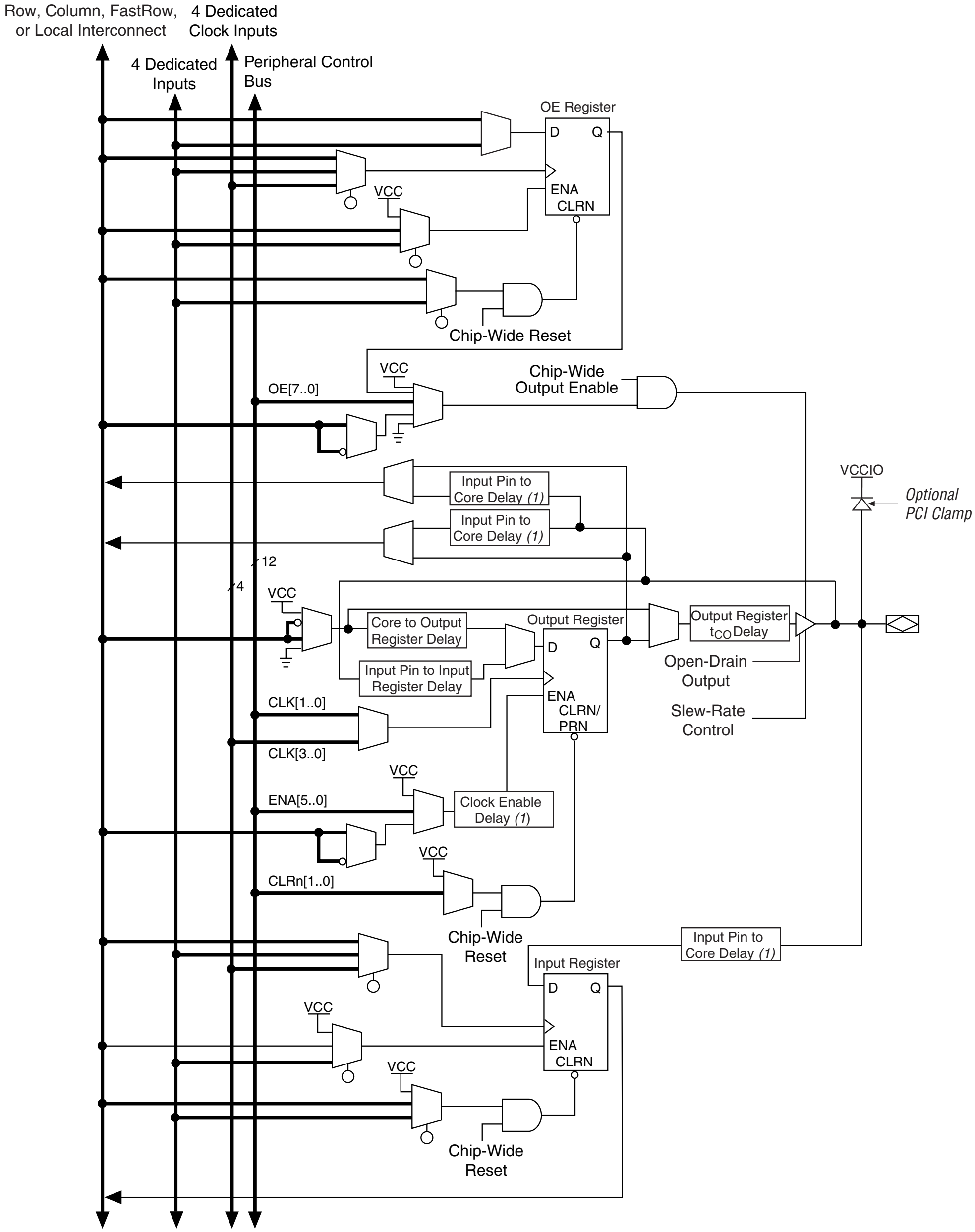
Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

Figure 26. APEX 20KE Bidirectional I/O Registers *Notes (1), (2)*

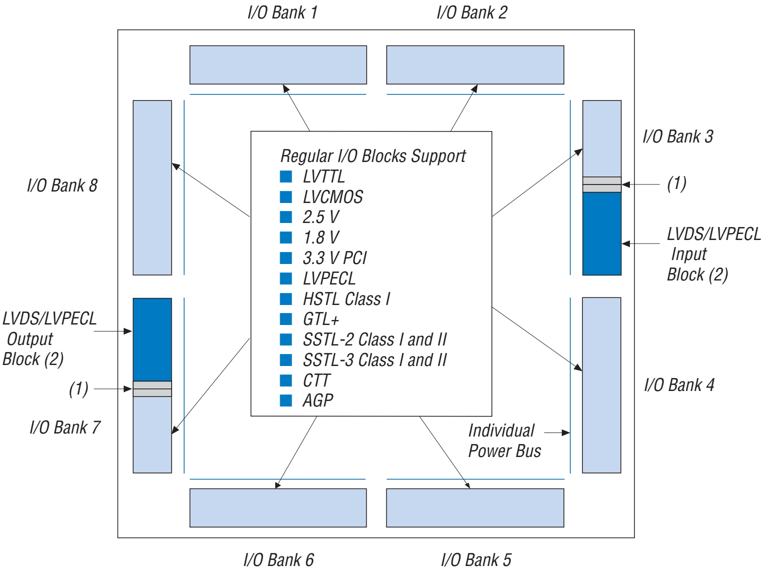


Notes to *Figure 26:*

(1) This programmable delay has four settings: off and three levels of delay.

(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Figure 29. APEX 20KE I/O Banks



Notes to Figure 29:

(1) For more information on placing I/O pins in LVDS blocks, refer to the *Guidelines for Using LVDS Blocks* section in *Application Note 120 (Using LVDS in APEX 20KE Devices)*.

(2) If the LVDS input and output blocks are not used for LVDS, they can support all of the I/O standards and can be used as input, output, or bidirectional pins with V_{CCIO} set to 3.3 V, 2.5 V, or 1.8 V.

Power Sequencing & Hot Socketing

Because APEX 20K and APEX 20KE devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

For more information, please refer to the “Power Sequencing Considerations” section in the *Configuring APEX 20KE & APEX 20KC Devices* chapter of the *Configuration Devices Handbook*.

Signals can be driven into APEX 20K devices before and during power-up without damaging the device. In addition, APEX 20K devices do not drive out during power-up. Once operating conditions are reached and the device is configured, APEX 20K and APEX 20KE devices operate as specified by the user.

Table 21. 32-Bit APEX 20K Device IDCODE

Device	IDCODE (32 Bits) *(1)*			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) *(2)*
EP20K30E	`0000`	`1000 0000 0011 0000`	`000 0110 1110`	1
EP20K60E	`0000`	`1000 0000 0110 0000`	`000 0110 1110`	1
EP20K100	`0000`	`0000 0100 0001 0110`	`000 0110 1110`	1
EP20K100E	`0000`	`1000 0001 0000 0000`	`000 0110 1110`	1
EP20K160E	`0000`	`1000 0001 0110 0000`	`000 0110 1110`	1
EP20K200	`0000`	`0000 1000 0011 0010`	`000 0110 1110`	1
EP20K200E	`0000`	`1000 0010 0000 0000`	`000 0110 1110`	1
EP20K300E	`0000`	`1000 0011 0000 0000`	`000 0110 1110`	1
EP20K400	`0000`	`0001 0110 0110 0100`	`000 0110 1110`	1
EP20K400E	`0000`	`1000 0100 0000 0000`	`000 0110 1110`	1
EP20K600E	`0000`	`1000 0110 0000 0000`	`000 0110 1110`	1
EP20K1000E	`0000`	`1001 0000 0000 0000`	`000 0110 1110`	1

Notes to Table 21:

(1) The most significant bit (MSB) is on the left.

(2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

Figure 31. APEX 20K JTAG Waveforms

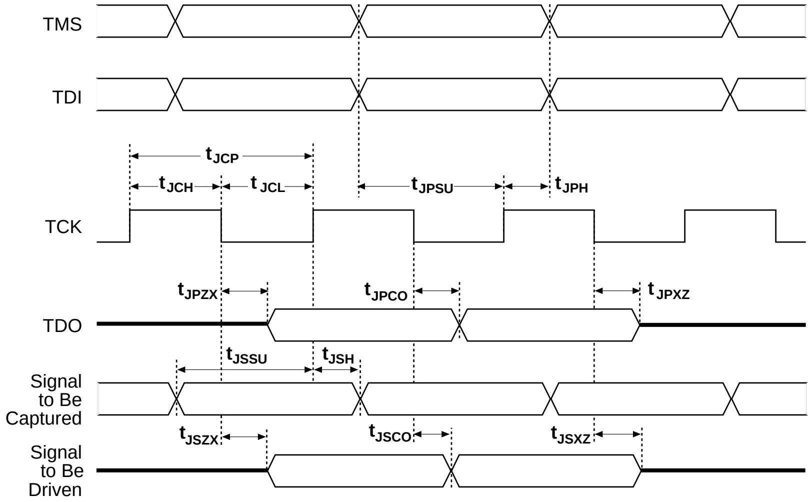


Table 22 shows the JTAG timing parameters and values for APEX 20K devices.

Table 22. APEX 20K JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	`TCK` clock period	100		ns
t_{JCH}	`TCK` clock high time	50		ns
t_{JCL}	`TCK` clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *Jam Programming & Test Language Specification*

Generic Testing

Each APEX 20K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20K devices are made under conditions equivalent to those shown in Figure 32. Multiple test patterns can be used to configure devices during all stages of the production flow.

Table 28. APEX 20KE Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(5)*, *(6)*	–0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices).*

Table 30. APEX 20KE Device Capacitance *Note (15)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 27 through 30:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

Vin	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
(9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when VCCIO = 1.8 V.
(10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(13) This value is specified for normal device operation. The value may vary during power-up.
(14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figures 38 and 39 show the asynchronous and synchronous timing waveforms, respectively, for the ESB macroparameters in Table 31.

Figure 38. ESB Asynchronous Timing Waveforms

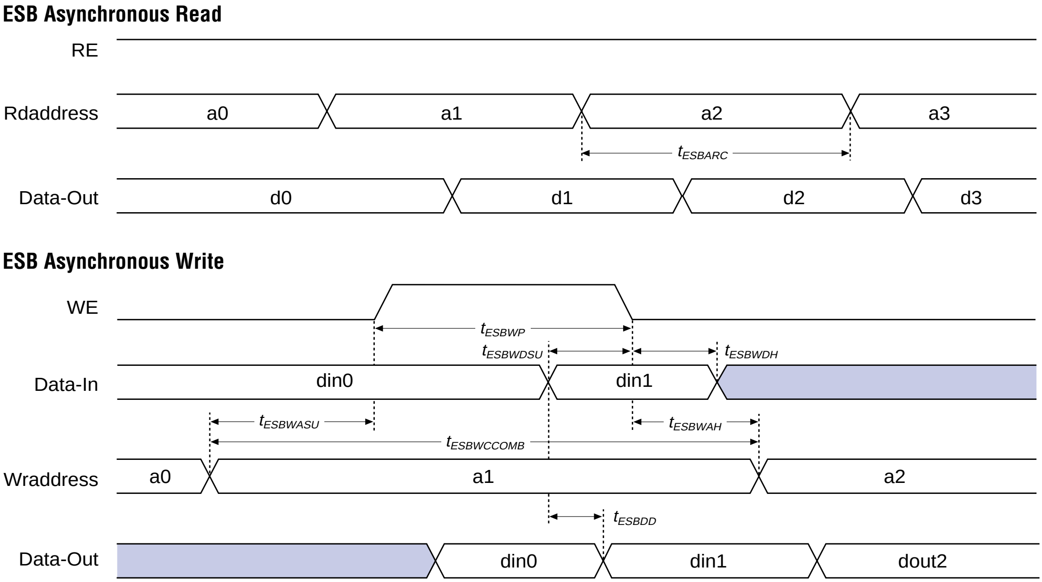
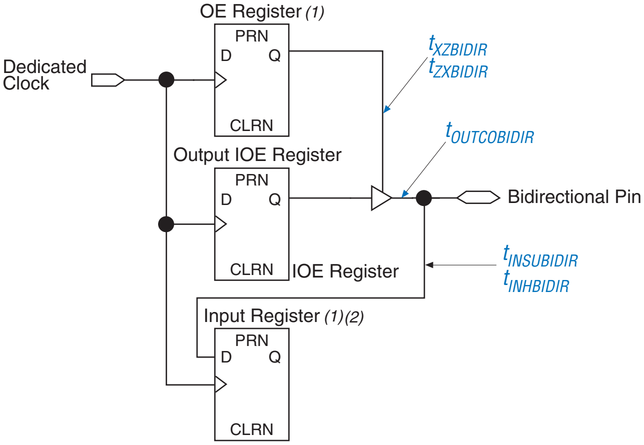


Figure 40. Synchronous Bidirectional Pin External Timing



Notes to Figure 40:

1. (1) The output enable and input registers are LE registers in the LAB adjacent to a bidirectional row pin. The output enable register is set with "Output Enable Routing= Signal-Pin" option in the Quartus II software.
2. (2) The LAB adjacent input register is set with "Decrease Input Delay to Internal Cells= Off". This maintains a zero hold time for lab adjacent registers while giving a fast, position independent setup time. A faster setup time with zero hold time is possible by setting "Decrease Input Delay to Internal Cells= ON" and moving the input register farther away from the bidirectional pin. The exact position where zero hold occurs with the minimum setup time, varies with device density and speed grade.

Table 31 describes the f_{MAX} timing parameters shown in Figure 36 on page 68.

Table 31. APEX 20K f_{MAX} Timing Parameters (Part 1 of 2)

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in
t_{ESBRC}	ESB Asynchronous read cycle time
t_{ESBWC}	ESB Asynchronous write cycle time
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBADDRSU}$	ESB address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers

Table 43. EP20K100 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	2.3		2.8		3.2		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	4.8	ns

Table 44. EP20K100 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (1)	2.3		2.8		3.2		ns
$t_{INHBIDIR}$ (1)	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
$t_{XZBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{ZXBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{INSUBIDIR}$ (2)	1.0		1.2		–		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	0.5	2.7	0.5	3.1	–	–	ns
$t_{XZBIDIR}$ (2)		4.3		5.0		–	ns
$t_{ZXBIDIR}$ (2)		4.3		5.0		–	ns

Table 45. EP20K200 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	1.9		2.3		2.6		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.6	2.0	5.6	2.0	6.8	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	–	ns

Notes to Tables 43 through 48:

(1) This parameter is measured without using ClockLock or ClockBoost circuits.
(2) This parameter is measured using ClockLock or ClockBoost circuits.

Tables 49 through 54 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K30E APEX 20KE devices.

Table 49. EP20K30E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.02		0.02		ns
t_H	0.11		0.16		0.23		ns
t_{CO}		0.32		0.45		0.67	ns
t_{LUT}		0.85		1.20		1.77	ns

Table 98. EP20K1000E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.78		2.02		1.95	ns
t_{ESBSRC}		2.52		2.91		3.14	ns
t_{ESBAWC}		3.52		4.11		4.40	ns
t_{ESBSWC}		3.23		3.84		4.16	ns
$t_{ESBWASU}$	0.62		0.67		0.61		ns
t_{ESBWAH}	0.41		0.55		0.55		ns
$t_{ESBWDSU}$	0.77		0.79		0.81		ns
t_{ESBWDH}	0.41		0.55		0.55		ns
$t_{ESBRASU}$	1.74		1.92		1.85		ns
t_{ESBRAH}	0.00		0.01		0.23		ns
$t_{ESBWESU}$	2.07		2.28		2.41		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.25		0.27		0.29		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.04		0.11		ns
$t_{ESBRADDRSU}$	0.14		0.11		0.16		ns
$t_{ESBDATACO1}$		1.29		1.50		1.63	ns
$t_{ESBDATACO2}$		2.55		2.99		3.22	ns
t_{ESBDD}		3.12		3.57		3.85	ns
t_{PD}		1.84		2.13		2.32	ns
$t_{PTERMSU}$	1.08		1.19		1.32		ns
$t_{PTERMCO}$		1.31		1.53		1.66	ns

Table 102. EP20K1000E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	3.22		3.33		3.51		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{XZBIDIR}$		6.31		7.09		7.76	ns
$t_{ZXBIDIR}$		6.31		7.09		7.76	ns
$t_{INSUBIDIRPL}^{L}$	3.25		3.26				ns
$t_{INHBIDIRPLL}$	0.00		0.00				ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.99			ns
$t_{XZBIDIRPLL}$		2.81		3.80			ns
$t_{ZXBIDIRPLL}$		2.81		3.80			ns

Tables 103 through 108 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1500E APEX 20KE devices.

Table 103. EP20K1500E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_H	0.25		0.25		0.25		ns
t_{CO}		0.28		0.32		0.33	ns
t_{LUT}		0.80		0.95		1.13	ns